NSN 5961-00-402-8161

Thyristor Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-00-402-8161

Inclosure Material:

Glass and metal

Overall Length:

0.404 inches

Overall Diameter:

Between 0.501 inches and 0.510 inches

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Anode

Mounting Method:

Terminal

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

480.0 nonrepetitive peak reverse voltage, peak total value and 400.0 repetitive peak reverse voltage, peak total value and 400.0 breakover voltage, dc and 2.0 gate trigger voltage, dc

Current Rating Per Characteristic:

900.00 amperes forward current, peak total value and 35.00 amperes forward current, total rms and 10.00 milliamperes breakover current, dc and 80.00 milliamperes gate trigger current, dc and 70.00 milliamperes holding current, dc

Power Rating Per Characteristic:

30.0 watts total device dissipation

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnpn

Test Data Document:

50985-8879600001 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

2 solder stud and 1 case

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0